

Features

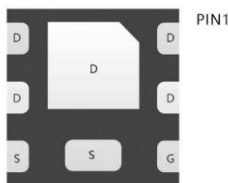
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Product Summary

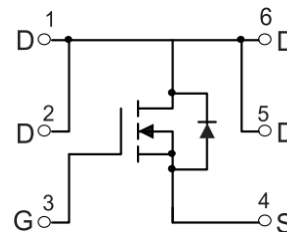
V_{DS}	$R_{DS(ON)}$ TYP	I_D
150V	250mΩ@10V	4A
	280mΩ@4.5V	

Application

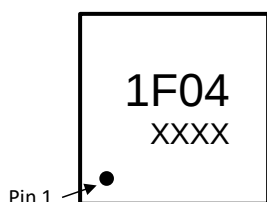
- Power switching application



DFN2X2-6L view



Schematic diagram



Pin 1

Marking and pin assignment

1F04 : Device code
 XXXX: Code
 Solid dot: Pin1 indicator



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	150	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_C=25^{\circ}C$ 4	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^{\circ}C$ 20	A
I_D	Continuous Drain Current	$T_C=25^{\circ}C$ 4	A
P_D	Maximum Power Dissipation	$T_C=25^{\circ}C$ 1.96	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	83.5	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSM1F04	DFN2X2-6L	1F04	3,000	45,000	180,000	7"reel

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	150	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =150V, V _{GS} =0V	--	--	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	--	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =4A	--	250	330	mΩ
		V _{GS} =4.5V, I _D =2A	--	280	450	mΩ

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)

C _{ISS}	Input Capacitance	V _{DS} =75V, V _{GS} =0V, f=1MHz	--	465	--	pF
C _{OSS}	Output Capacitance		--	23	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	14	--	pF

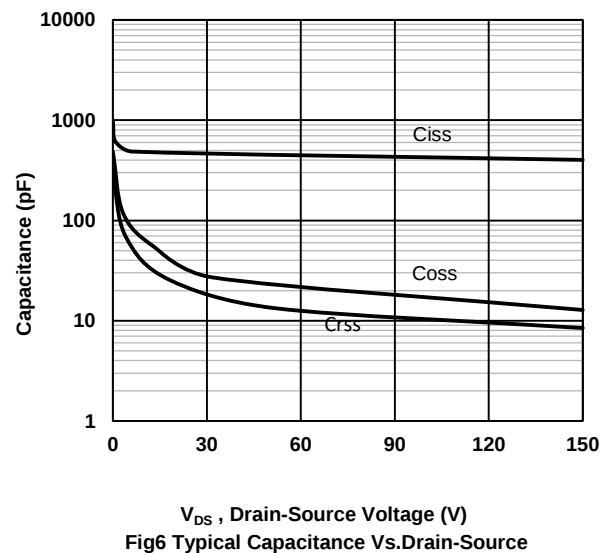
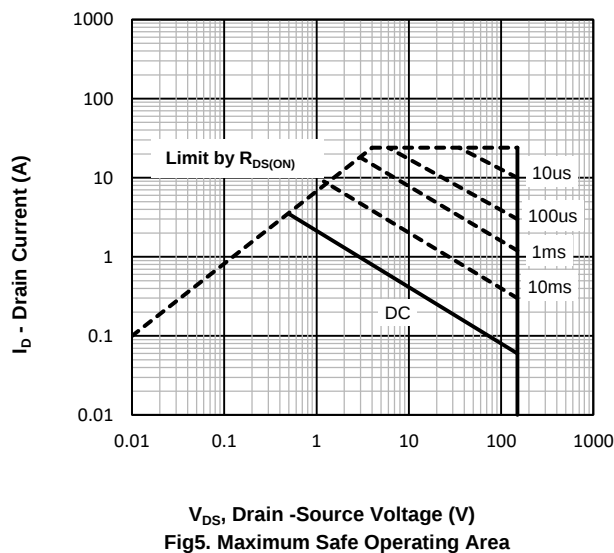
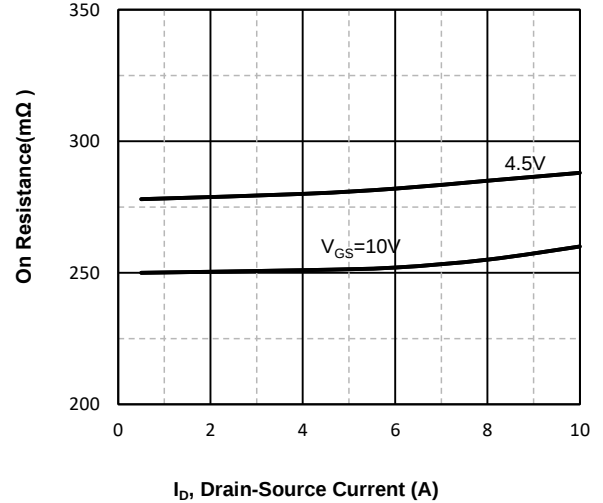
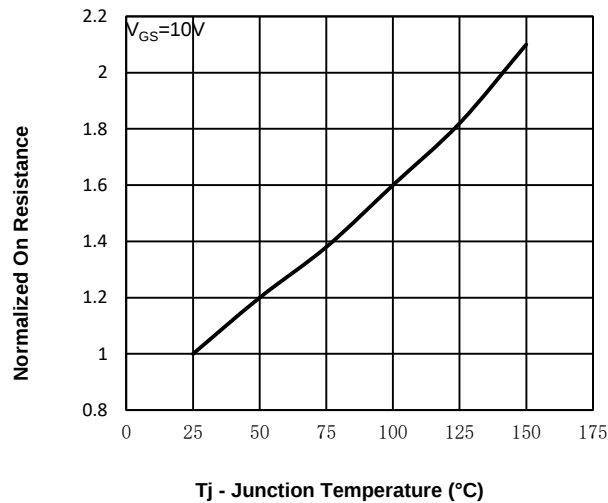
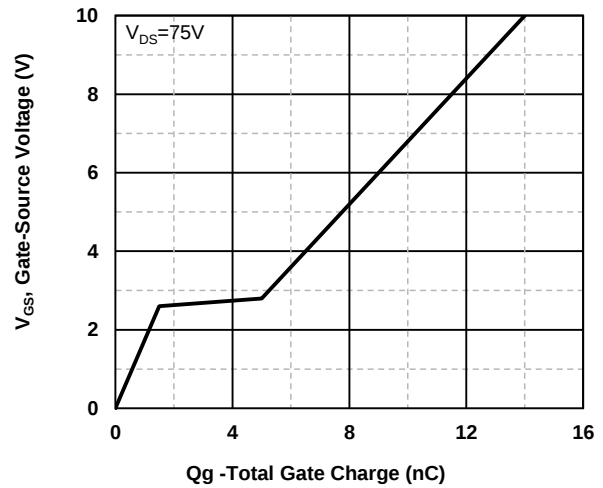
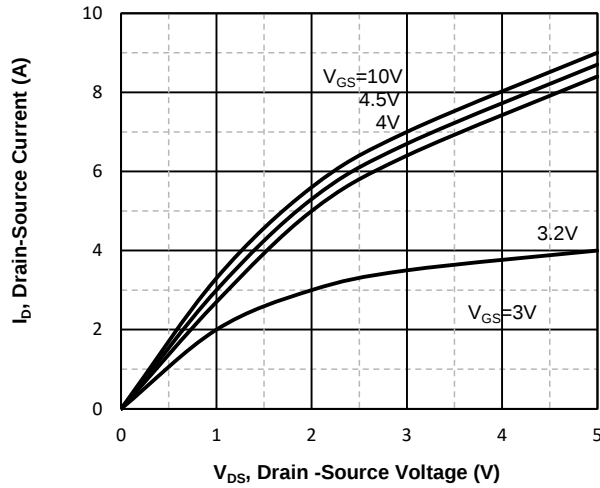
Switching Characteristics

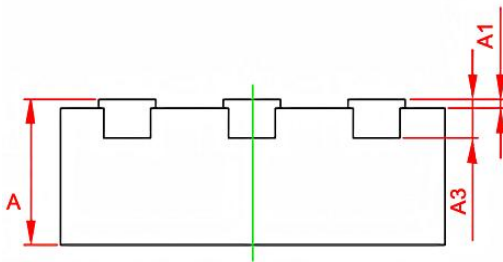
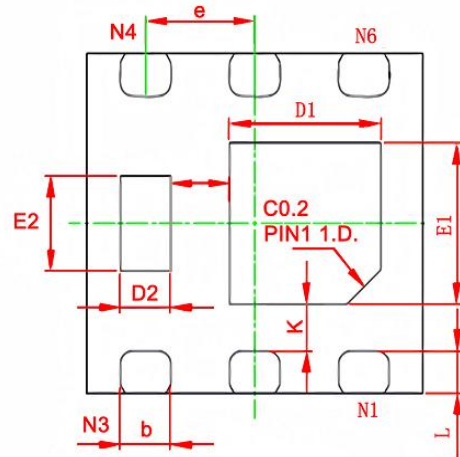
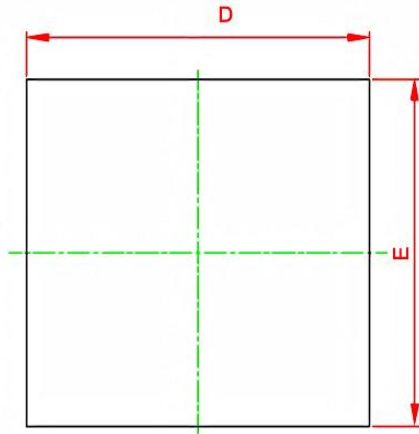
Q _g	Total Gate Charge	V _{DS} =75V, I _D =4A, V _{GS} =10V	--	14	--	nC
Q _{gs}	Gate Source Charge		--	1.6	--	nC
Q _{gd}	Gate Drain Charge		--	4	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =75V, I _D =4A, V _{GS} =10V, R _G =3Ω	--	5.8	--	nS
t _r	Turn-on Rise Time		--	2.2	--	nS
t _{d(off)}	Turn-Off Delay Time		--	16.9	--	nS
t _f	Turn-Off Fall Time		--	2.6	--	nS

Source- Drain Diode Characteristics

V _{SD}	Forward on voltage	T _J =25°C, I _S =4A	--	--	1.2	V
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Typical Operating Characteristics



DFN2X2-6L Package information


Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.600	0.700	0.023	0.027
A1	0.000	0.050	0.000	0.001
A3	0.203REF		0.007REF	
b	0.315	0.415	0.012	0.016
D	1.924	2.076	0.075	0.081
E	1.924	2.076	0.075	0.081
e	0.650TYP		0.225TYP	
L	0.224	0.376	0.008	0.014
k	0.200	-	0.007	-
E1	1.000	1.200	0.039	0.047
D1	0.900	1.100	0.035	0.043
E2	0.700	0.900	0.027	0.035
D2	0.150	0.350	0.005	0.013